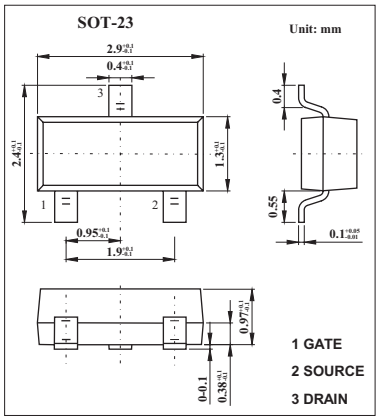
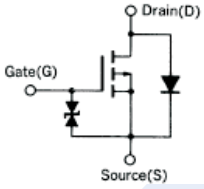
MOS Fied Effect Transistor

2SJ185



Features

- Directly driven by Ics having a 3V poer supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage VGS=0	VDSS	-50	V
Gate to source voltage VDS=0	VGSS	±7.0	V
Drain current (DC)	ID	±100	mA
Drain current(pulse) *	ID	±200	mA
Power dissipation	PD	200	mW
Operating temperature	Topt	-55 to +80	℃
Storage temperature	Tstg	-55 to +150	℃

* PW ⩽ 10 ms; d ⩽ 50%.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	IDSS	VDS=-50V,VGS=0			-10	μA
Gate leakage current	IGSS	VGS=±7.0V,VDS=0			±5	μA
Gate cut-off voltage	VGS(off)	VDS=-3V,ID=-1μA	-1.2	-1.6	-2.0	V
Forward transfer admittance	|Yfs|	VDS=-3V,ID=-10mA	20	42		ms
Drain to source on-state resistance	RDS(on)	VGS=-2.5V,ID=-1mA		25	40	Ω
		VGS=-4.0V,ID=-10mA		13	20	Ω
Input capacitance	Ciss	VDS=-3V,VGS=0,f=1MHZ		22		pF
Output capacitance	Coss			12		pF
Reverse transfer capacitance	Crss			4		pF
Turn-on delay time	td(on)	VGS(on)=-3V,RG=10Ω,VDD=-3V,ID=-20mA RL=150Ω		80		ns
Rise time	tr			230		ns
Turn-off delay time	td(off)			40		ns
Fall time	tf			70		ns

Marking

Marking	H12